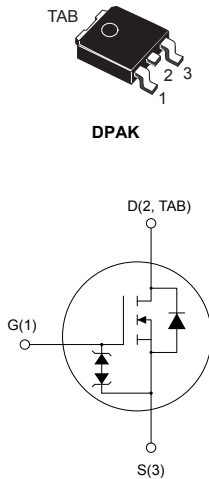


N-channel 620 V, 1.7 Ω typ., 3.8 A MDmesh K3 Power MOSFET in a DPAK package



AM01476v1_tab



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STD4N62K3	620 V	2.0 Ω	3.8 A

- 100% avalanche tested
- Extremely high dv/dt capability
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Applications

- Switching applications

Description

This MDmesh K3 Power MOSFET is the result of improvements applied to STMicroelectronics' MDmesh technology, combined with a new optimized vertical structure. This device boasts an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering it suitable for the most demanding applications.

Product status link

[STD4N62K3](#)

Product summary

Order code	STD4N62K3
Marking	4N62K3
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	620	V
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	3.8	A
	Drain current (continuous) at $T_C = 100\text{ °C}$	2	
$I_{DM}^{(1)}$	Drain current (pulsed)	15.2	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	70	W
I_{AR}	Avalanche current, repetitive or not-repetitive	3.8	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	115	mJ
ESD	Gate-source human body model ($R = 1.5\text{ k}\Omega$, $C = 100\text{ pF}$)	2.5	kV
$dv/dt^{(3)}$	Peak diode recovery voltage slope	12	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Maximum operating junction temperature		°C

1. Pulse width limited by safe operating area.
2. Starting $T_J = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.
3. $I_{SD} \leq 3.8\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$. $V_{DS}(\text{peak}) \leq V_{(BR)DSS}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.79	°C/W
$R_{thJA}^{(1)}$	Thermal resistance, junction-to-ambient	50	°C/W

1. When mounted on 1 inch² FR-4, 2 Oz copper board.

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 3. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	620			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 620\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 620\text{ V}$, $T_C = 125\text{ °C}$ ⁽¹⁾			50	μA
I_{GSS}	Gate body leakage current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.9\text{ A}$		1.7	2.0	Ω

1. Specified by design, not tested in production.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$		550		pF
C_{oss}	Output capacitance			42		pF
C_{rss}	Reverse transfer capacitance			7		pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ to }496\text{ V}$		27		pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	2	5	10	Ω
Q_g	Total gate charge	$V_{DD} = 496\text{ V}$, $I_D = 3.8\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 15. Test circuit for gate charge behavior)		22		nC
Q_{gs}	Gate-source charge			4		nC
Q_{gd}	Gate-drain charge			13		nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 1.9\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	10	-	ns
t_r	Rise time		-	9	-	ns
$t_{d(off)}$	Turn-off delay time		-	29	-	ns
t_f	Fall time		-	19	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		3.8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		15.2	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 3.8 \text{ A}, V_{GS} = 0 \text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 3.8 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, V_{DD} = 60 \text{ V}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	220		ns
Q_{rr}	Reverse recovery charge		-	1.4		μC
I_{RRM}	Reverse recovery current		-	13		A
t_{rr}	Reverse recovery time	$I_{SD} = 3.8 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, V_{DD} = 60 \text{ V},$ $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	270		ns
Q_{rr}	Reverse recovery charge		-	1.9		μC
I_{RRM}	Reverse recovery current		-	14		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

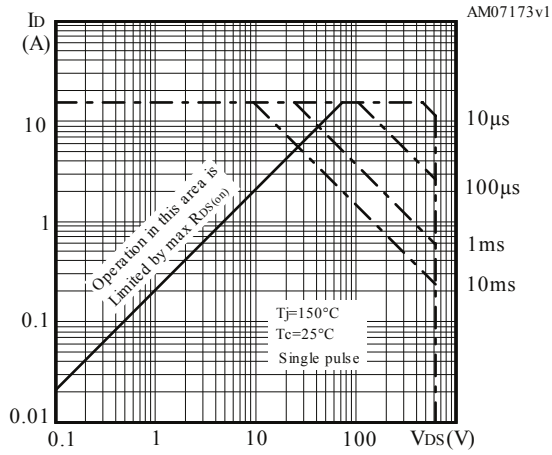


Figure 2. Normalized transient thermal impedance

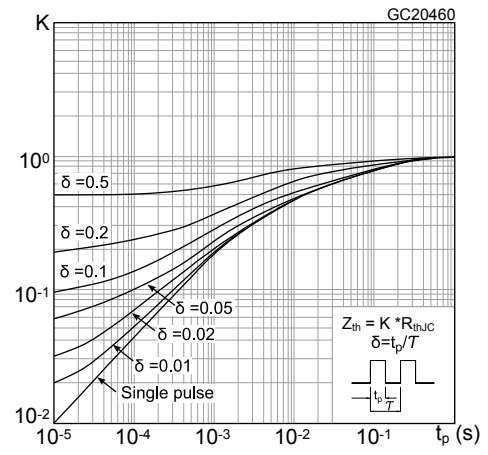


Figure 3. Typical output characteristics

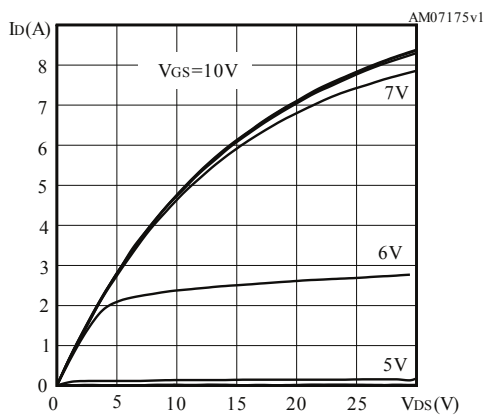


Figure 4. Typical transfer characteristics

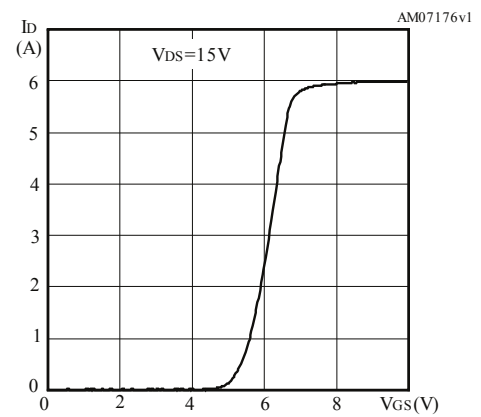


Figure 5. Typical gate charge characteristics

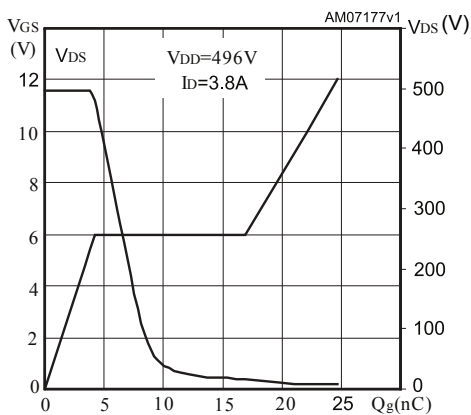


Figure 6. Typical drain-source on-resistance

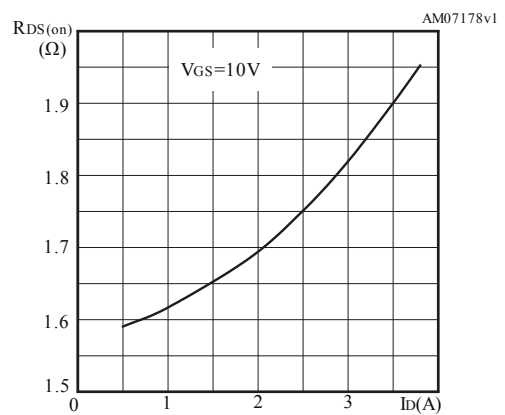


Figure 7. Typical capacitance characteristics

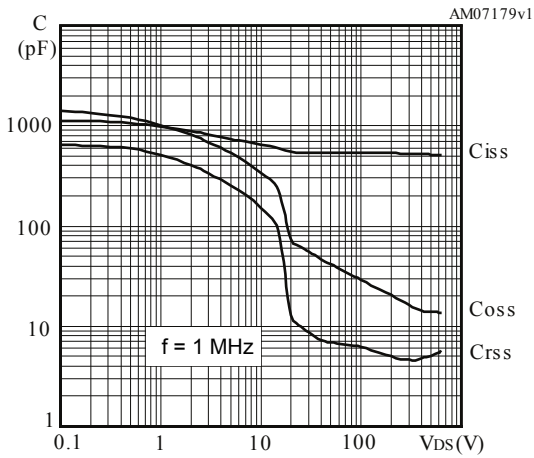


Figure 8. Typical output capacitance stored energy

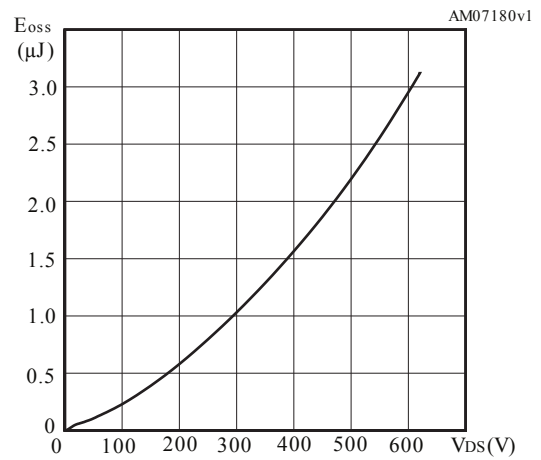


Figure 9. Normalized gate threshold vs temperature

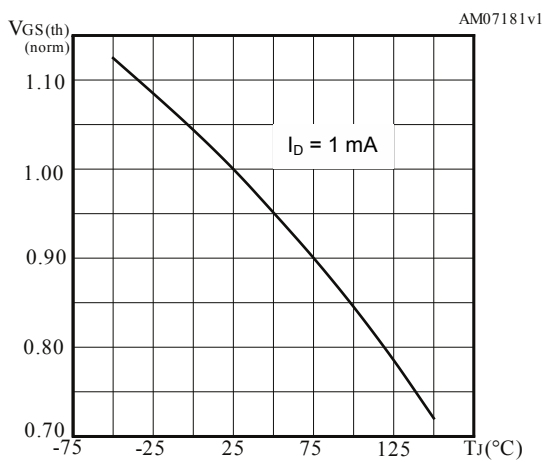


Figure 10. Normalized on-resistance vs temperature

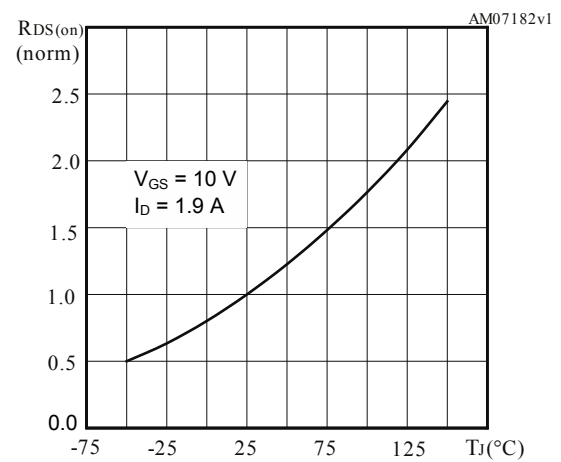


Figure 11. Normalized breakdown voltage vs temperature

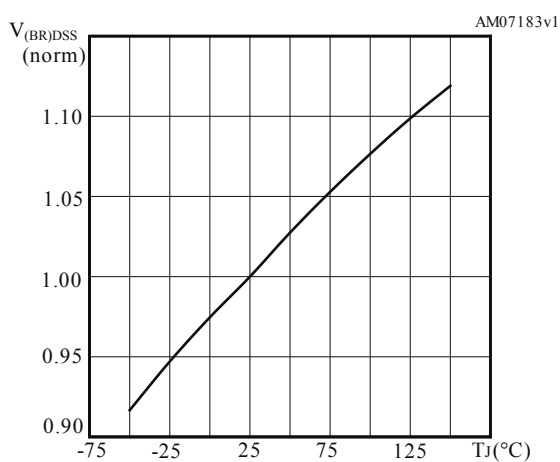


Figure 12. Typical reverse diode forward characteristics

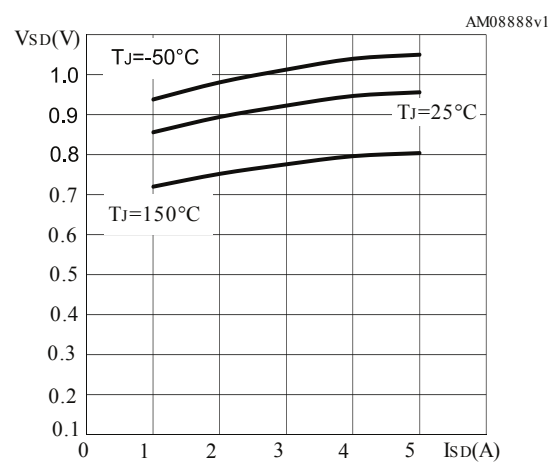
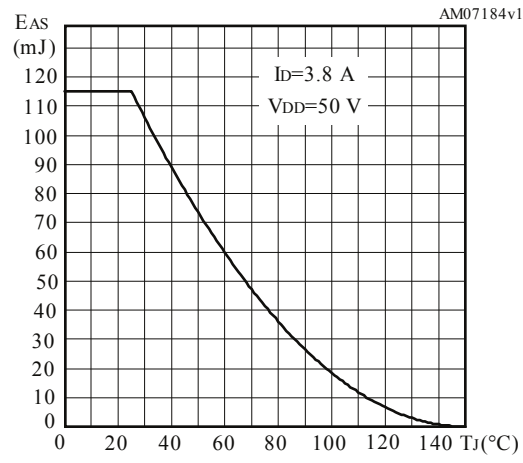
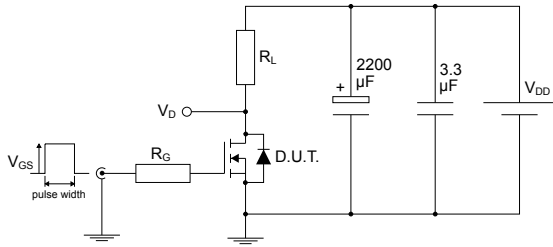


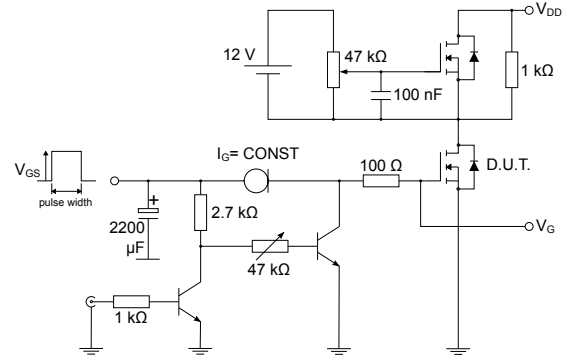
Figure 13. Maximum avalanche energy vs starting T_J



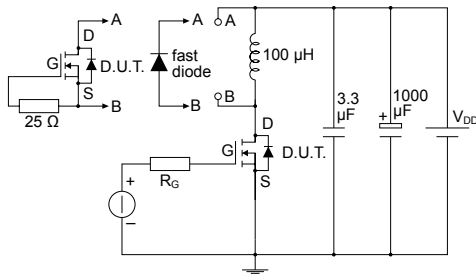
3 Test circuits

Figure 14. Test circuit for resistive load switching times


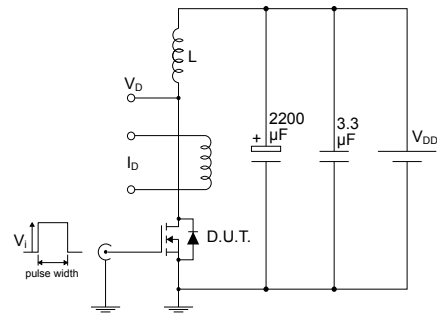
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Figure 15. Test circuit for gate charge behavior


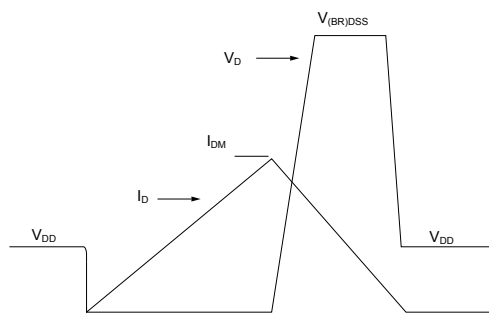
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Figure 16. Test circuit for inductive load switching and diode recovery times


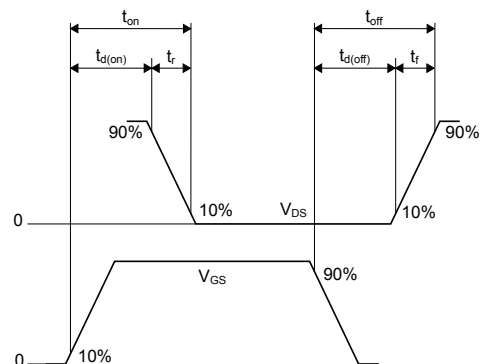
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Figure 17. Unclamped inductive load test circuit


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Figure 18. Unclamped inductive waveform


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Figure 19. Switching time waveform


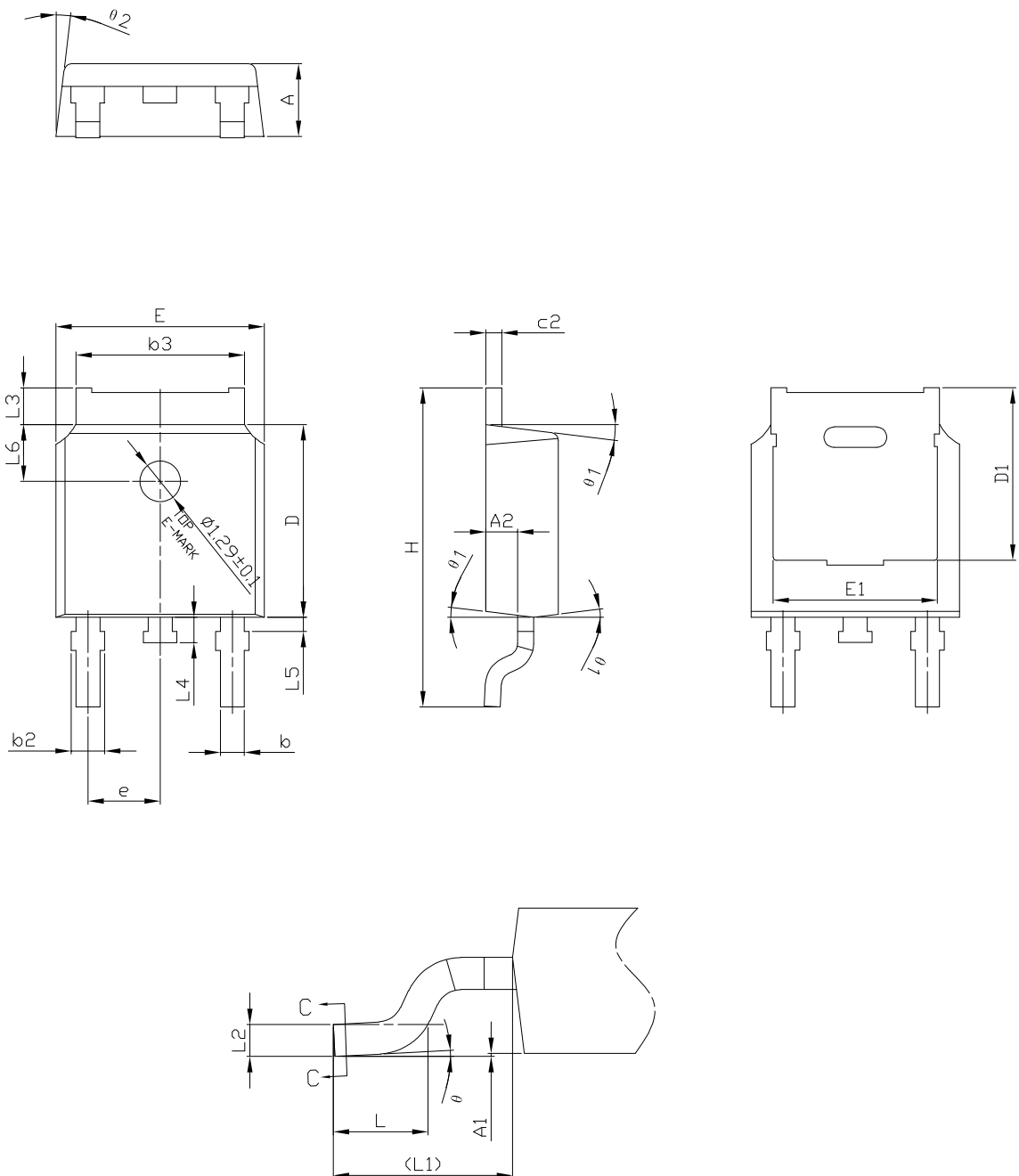
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type C3 package information

Figure 20. DPAK (TO-252) type C3 package outline



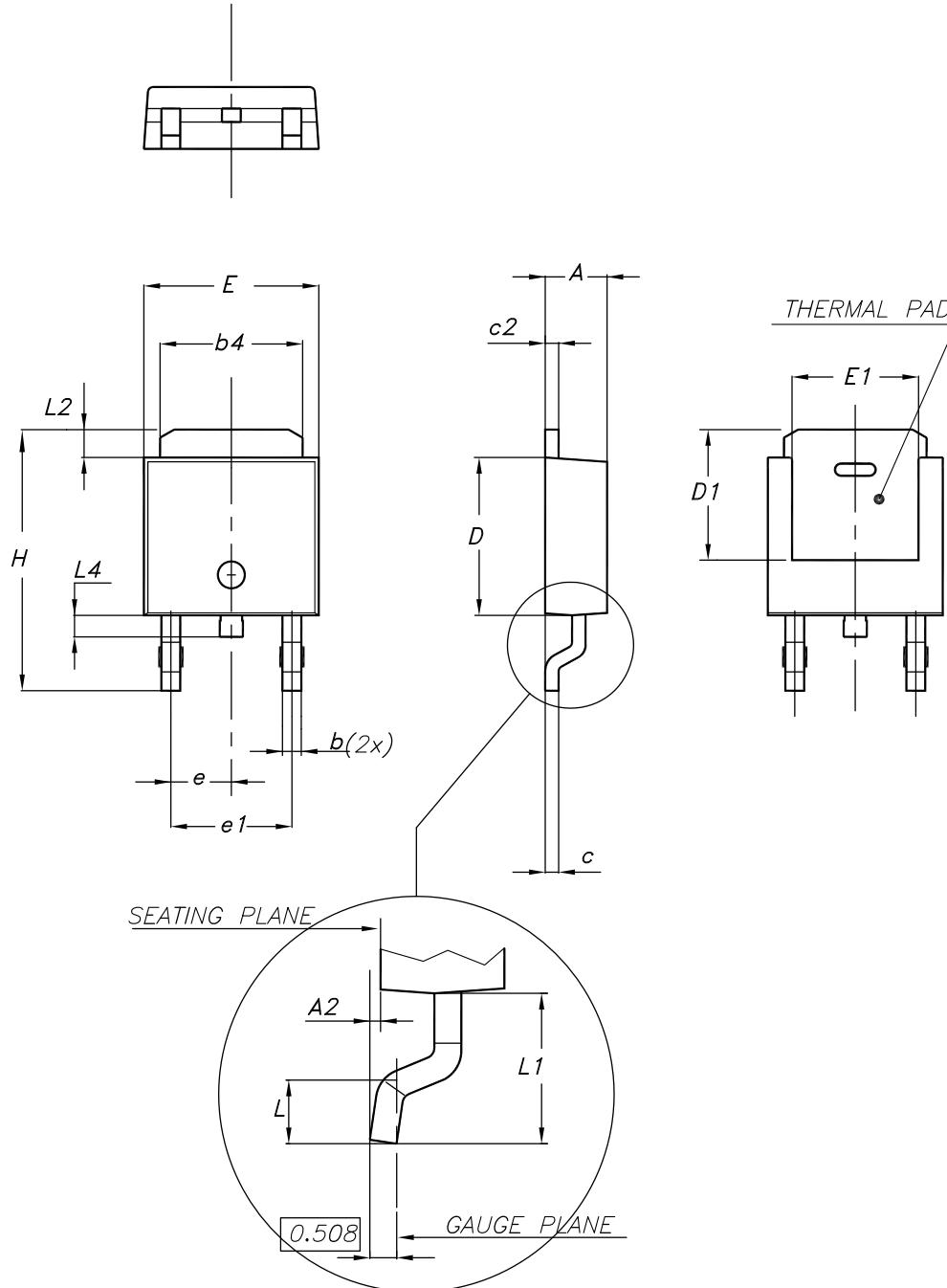
0068772_type-C3_rev34

Table 7. DPAK (TO-252) type C3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.00		0.10
A2	0.90	1.01	1.10
b	0.72		0.85
b2	0.72		1.10
b3	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.20	5.45	5.70
E	6.50	6.60	6.70
E1	5.00	5.20	5.40
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.51 BSC		
L3	0.90		1.25
L4	0.60	0.80	1.00
L5	0.15		0.75
L6	1.80 REF		
θ	0°		8°
θ1	5°	7°	9°
θ2	5°	7°	9°

4.2 DPAK (TO-252) type E package information

Figure 21. DPAK (TO-252) type E package outline

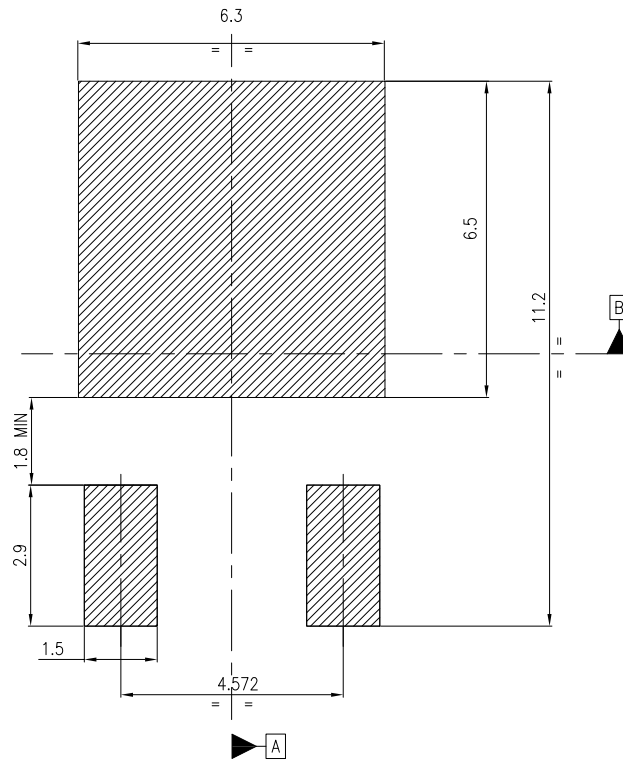


0068772_typeE_rev.34

Table 8. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 22. DPAK (TO-252) recommended footprint (dimensions are in mm)



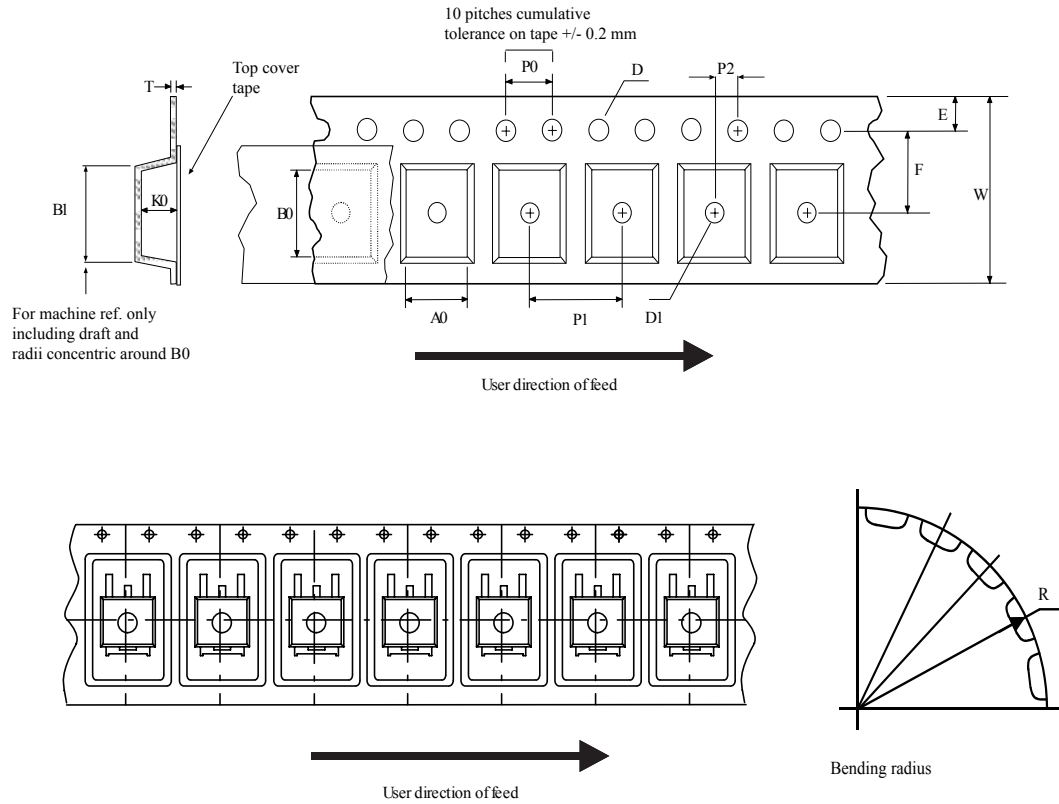
Notes:

- 1) This footprint is able to ensure insulation up to 630 Vrms (according to CEI IEC 664-1)
- 2) The device must be positioned within $\oplus 0.05$ A B

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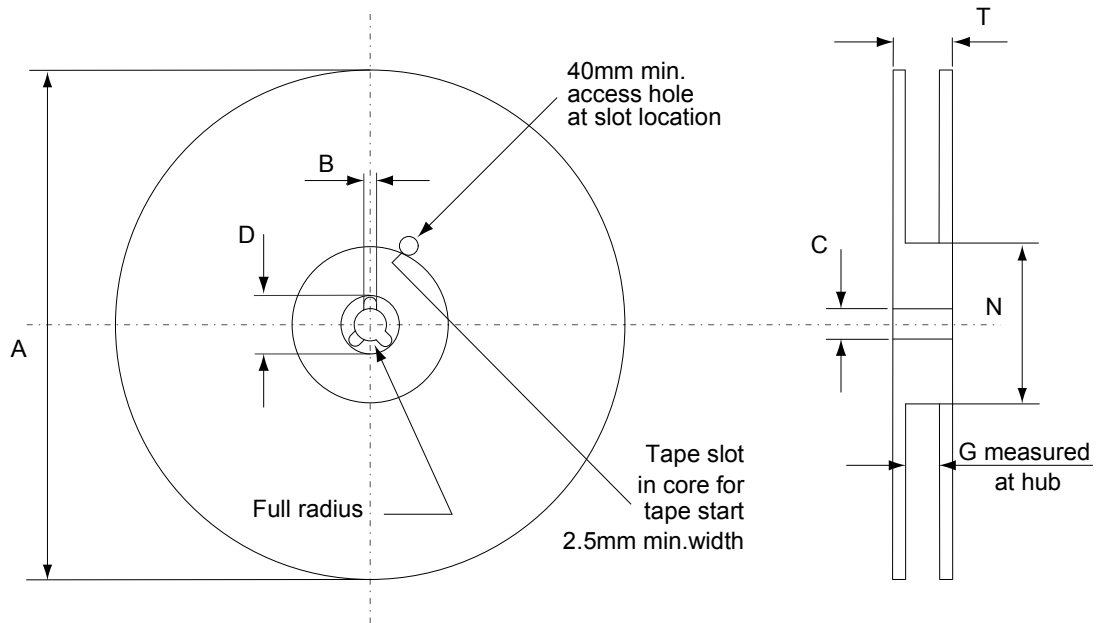
4.3 DPAK (TO-252) packing information

Figure 23. DPAK (TO-252) tape outline



AM08852v1

Figure 24. DPAK (TO-252) reel outline



AM06038v1

Table 9. DPAK (TO-252) tape and reel mechanical data

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1		Base qty.	2500
P1	7.9	8.1		Bulk qty.	2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 10. Document revision history

Date	Revision	Changes
16-Dec-2010	1	First release.
26-Apr-2012	2	Added min and max values for RG in Table 5: Dynamic and Section 5: Packaging mechanical data. Updated Section 4: Package mechanical data. Minor text changes.
09-Sep-2013	3	– Updated: <i>Section 4: Package mechanical data</i> – Minor text changes
03-Aug-2018	4	The part number STB4N62K3 has been moved to a separate datasheet. Removed maturity status indication from cover page. The document status is production data. Updated title and features in cover page. Updated <i>Section 1 Electrical ratings</i> , <i>Section 2 Electrical characteristics</i> and <i>Section 4 Package information</i> . Minor text changes.
04-Jul-2023	5	Modified the entire <i>Section 4 Package information</i> . Minor text changes.

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